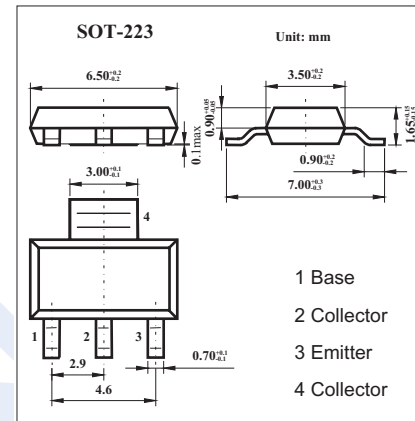


2.0W Surface Mount Complementary PNP Silicon Power Transistor KZT2955 (CZT2955)

■ Features

- High current (max. 6A).
- Low voltage (max. 60V).



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|--|------------------|-------------|------|
| Collector-base voltage | V _{CB0} | -100 | V |
| Collector - emitter votage | V _{CER} | -70 | V |
| Collector-emitter voltage | V _{CEO} | -60 | V |
| Emitter-base voltage | V _{EBO} | -7 | V |
| Collector current | I _C | -6 | A |
| Base current | I _B | -3 | A |
| Power dissipation | P _D | 2 | W |
| Thermal resistance,Junction-to-ambient | R _{θJA} | 62.5 | °C/W |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -65 to +150 | °C |

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|---|----------------------|---|-----|-----|------|------|
| Collector to emitter breakdown voltage | V _{CEO} | I _C =-30mA | -60 | | | V |
| Collector to emitter breakdown voltage | V _{CER} | I _C =-30mA,R _{BE} =100 Ω | -70 | | | V |
| Collctor cutoff current | I _{CEO} | V _{CE} =-30V | | | -700 | μ A |
| | I _{CEV} | V _{CE} =-100V,V _{EB} =-1.5V | | | 1.0 | mA |
| Emitter cutoff current | I _{EBO} | V _{EB} = -7.0 V | | | -5.0 | m A |
| DC current gain | h _{FE} | I _C = -4.0A; V _{CE} = -4.0 V | 20 | | 70 | |
| | | I _C = -6.0A; V _{CE} = -4.0V | 5.0 | | | |
| Collector to emitter saturation voltage | V _{CE(sat)} | I _C = -4.0A; I _B = -400mA | | | -1.1 | V |
| Base to emitter ON voltage | V _{BE(on)} | V _{CE} =-4.0V,I _C =-4.0A | | | -1.5 | V |
| Transition frequency | f _T | I _C =- 500mA; V _{CE} =-10V; f = 1.0 MHz | 2.5 | | | MHz |